

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | I_D (A) | Q_g (Typ) |
|-------------------|---------------------------|-----------------|-------------|
| 60 | 0.005 at $V_{GS} = 10$ V | 90 ^d | 105 |

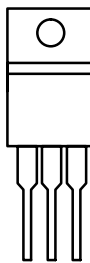
FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g and UIS Tested


RoHS
COMPLIANT

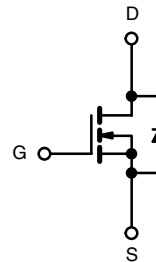
APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- Industrial
- OR-ing

TO-220AB


G D S

Top View

Ordering Information: SUP90N06-5m0P-E3 (Lead (Pb)-free)


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit | |
|--|----------------|----------------------------|------------------|---|
| Drain-Source Voltage | V_{DS} | 60 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current ($T_J = 175$ °C) | I_D | $T_C = 25$ °C | 90 ^d | A |
| | | $T_C = 70$ °C | 90 ^d | |
| Pulsed Drain Current | I_{DM} | 240 | | |
| Avalanche Current | I_{AS} | 70 | | |
| Single Avalanche Energy ^a | E_{AS} | 245 | mJ | |
| Maximum Power Dissipation ^a | P_D | $T_C = 25$ °C | 300 ^b | W |
| | | $T_A = 25$ °C ^c | 3.75 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | °C | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Limit | Unit |
|--|------------|-------|------|
| Junction-to-Ambient (PCB Mount) ^c | R_{thJA} | 40 | °C/W |
| Junction-to-Case (Drain) | R_{thJC} | 0.5 | |

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.

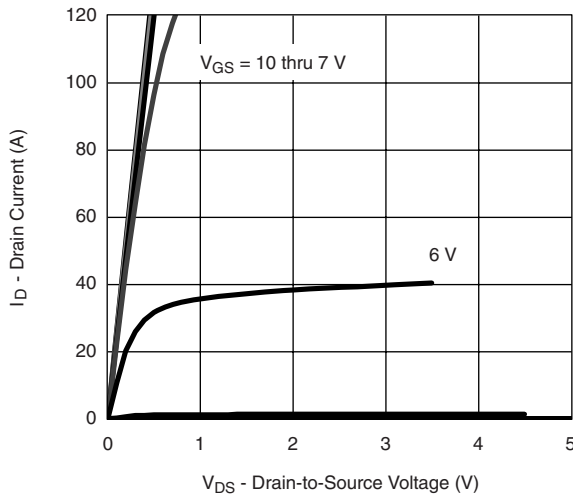
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|---------------|--|-----|--------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 60 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2.5 | | 4.5 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 250 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | | 50 | |
| | | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$ | 70 | | | A |
| Drain-Source On-State Resistance ^a | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | | 0.0041 | 0.005 | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 0.0068 | 0.0087 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 20\text{ A}$ | | 60 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$ | | 6190 | | μF |
| Output Capacitance | C_{oss} | | | 990 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 340 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$ | | 105 | 160 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 29 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 28 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 1.4 | 2.8 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 30\text{ V}, R_L = 0.4\text{ }\Omega$ $I_D \approx 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 23 | 35 | ns |
| Rise Time ^c | t_r | | | 15 | 25 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 36 | 55 | |
| Fall Time ^c | t_f | | | 8 | 15 | |
| Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b | | | | | | |
| Continuous Current | I_S | | | | 85 | A |
| Pulsed Current | I_{SM} | | | | 240 | |
| Forward Voltage ^a | V_{SD} | $I_F = 30\text{ A}, V_{GS} = 0\text{ V}$ | | 0.84 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 61 | 100 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 3.0 | 4.5 | A |
| Reverse Recovery Charge | Q_{rr} | | | | 91 | 140 |

Notes:

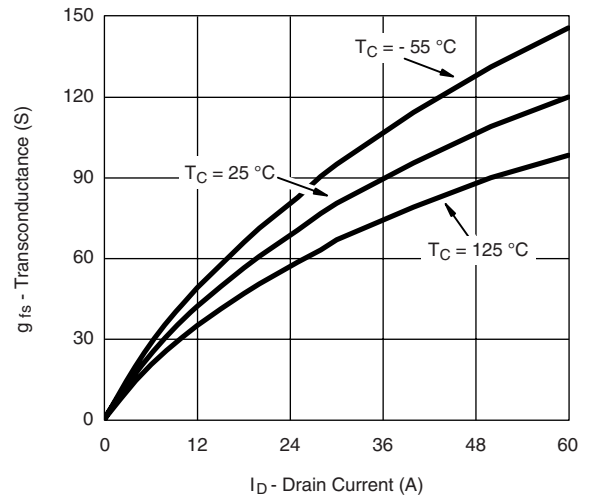
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

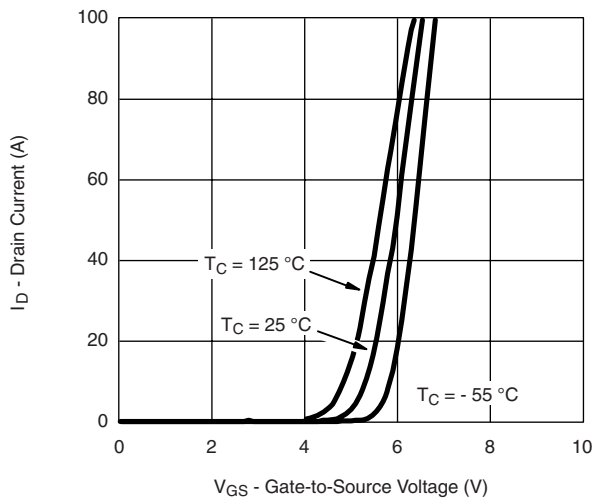
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



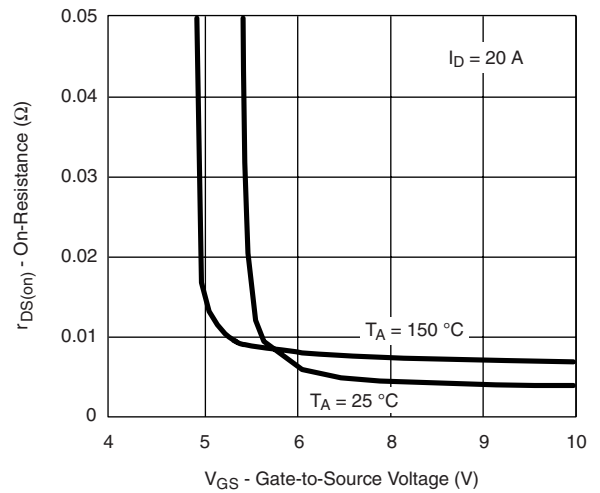
Output Characteristics



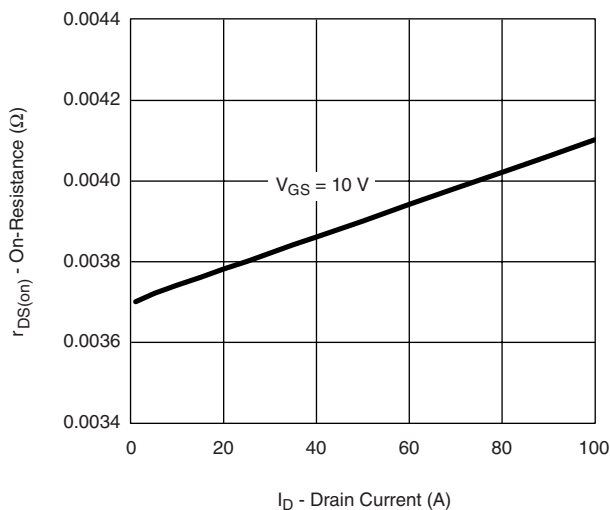
Transconductance



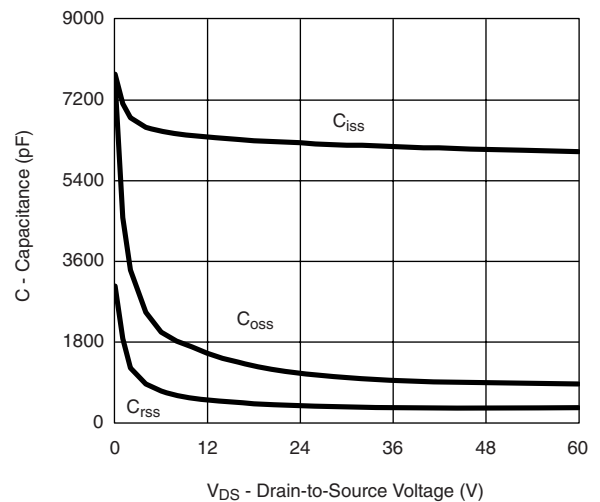
Transfer Characteristics



On-resistance vs. Gate-to-Source Voltage

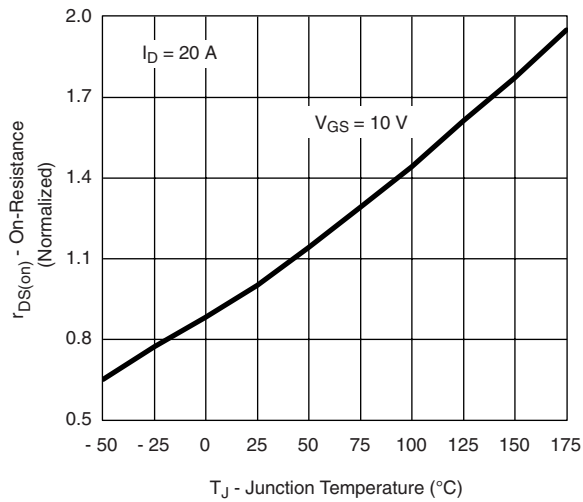


On-Resistance vs. Drain Current

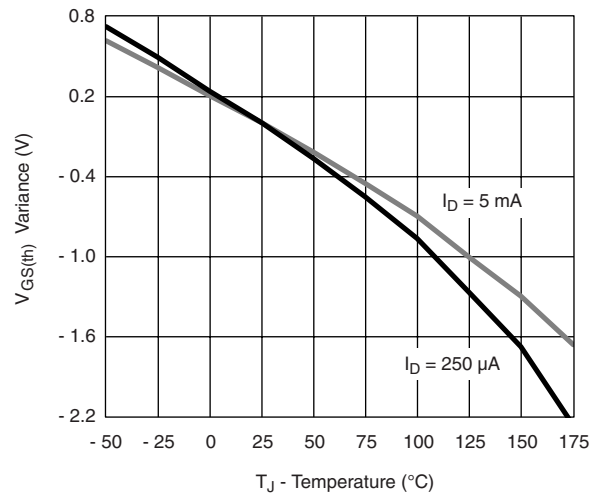


Capacitance

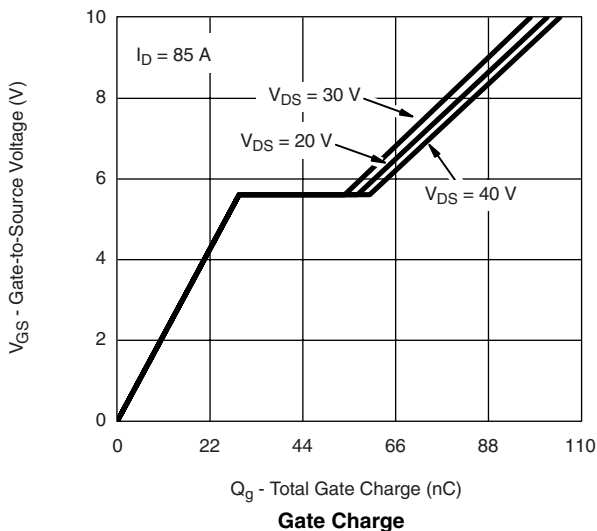
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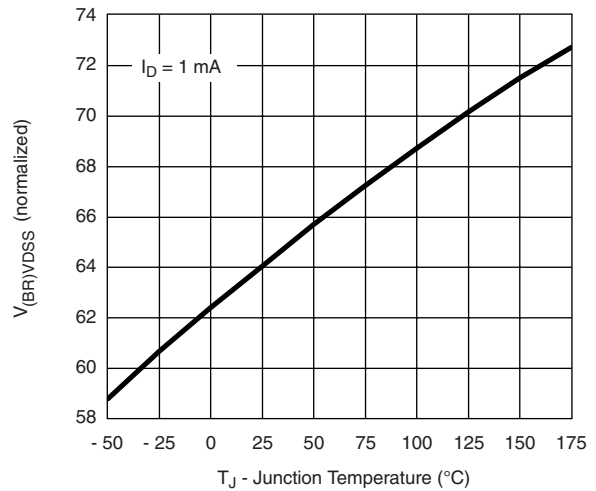
On-Resistance vs. Junction Temperature



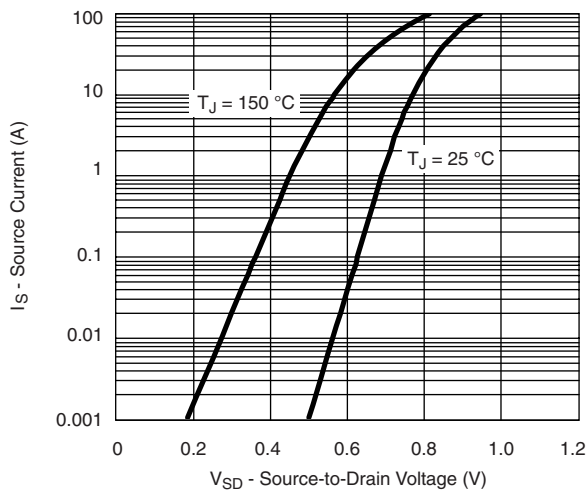
Threshold Voltage



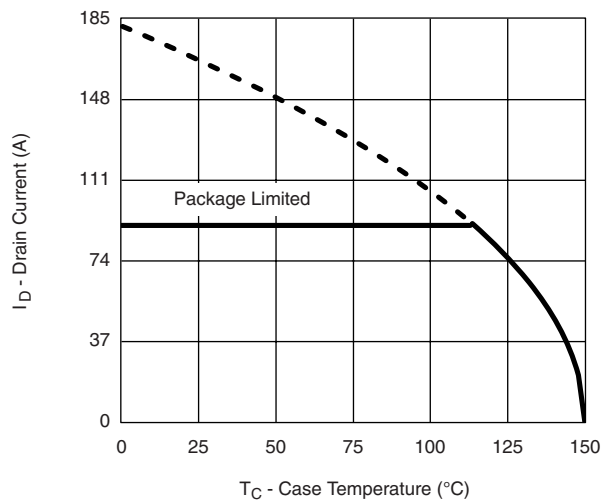
Gate Charge



On-Resistance vs. Junction Temperature

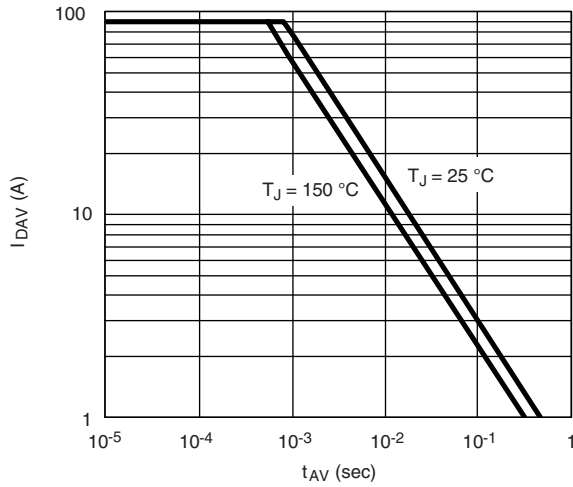


Source-Drain Diode Forward Voltage

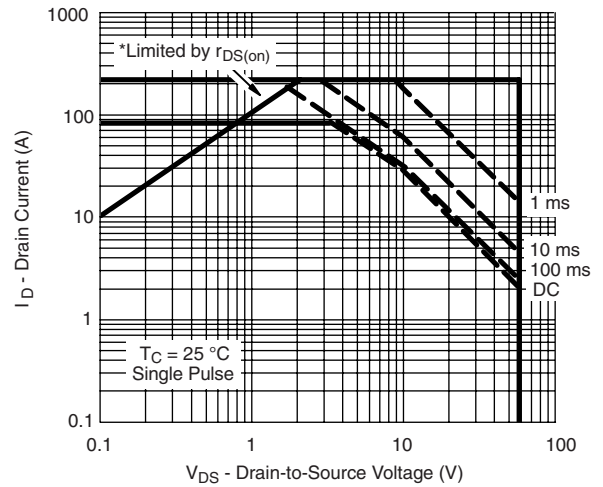


Maximum Drain Current vs. Case Temperature

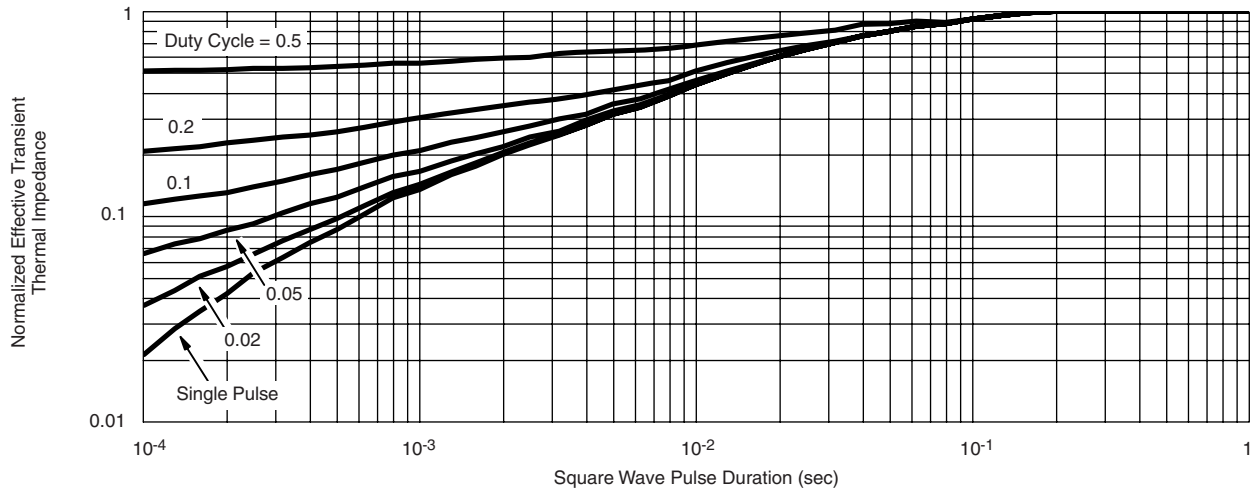
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

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